

Appl No. 10/762,122
Amdt. dated Mar. 14, 2005
Reply to Office action of Dec. 13, 2004

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

- 1-15. (cancelled)
16. (currently amended) A method for forming a leadframe for use in the assembly of integrated circuit devices, comprising:
providing a base metal structure;
forming a nickel layer on the metal structure;
forming a matte, coarse grain, tin solder layer on the nickel layer selectively, covering an area of said leadframe for attaching a integrated circuit chip; and
forming a palladium or silver layer selectively, covering an area of said leadframe suitable for attaching a bonding wire.
17. (previously presented) The method in Claim 16 wherein the base metal structure includes copper, copper alloy, aluminum, iron-nickel alloy, or invar.
18. (canceled)
- 19 (currently amended) The method in Claim [18] 16 wherein said tin solder has a reflow temperature of 232 °C.
20. (currently amended) The method in Claim [18] 16 wherein the solder layer has a thickness in the range from about 4.0 to 6.0 µm.
21. (previously presented) The method in Claim 16 wherein said palladium or silver layer has a thickness in the range from about 20 to 60 nm.

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22. (currently amended) A method for forming a leadframe for use with integrated circuit chips comprising:
- providing a base metal structure having a plated layer of nickel fully covering said base metal;
 - forming a layer of matte, coarse grain, pure tin on said nickel layer selectively, covering an area of said leadframe suitable for attaching a circuit chip; and
 - forming a layer of palladium or silver on said nickel layer selectively, covering an area of said leadframe suitable for attaching a bonding wire.

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23. (currently amended) A method for forming a semiconductor device comprising:
- providing a leadframe including a chip-mount pad and a lead segment having a first end near said mount pad and a second end remote from said mount pad;
 - forming a nickel layer over said leadframe;
 - forming a layer of palladium on said nickel layer selectively, covering said first end of said lead segment;
 - attaching an integrated circuit chip to said mount pad; and
 - applying a layer of matte, coarse grain, pure tin solder selectively, covering said second end of said lead segment.
24. (previously presented) The method in Claim 23 further comprising bending the lead segment suitable for solder attachment.

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